



### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	15mΩ @ V <sub>GS</sub> = 10V	10.0A
000	$21.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	8.4A

#### **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Description**

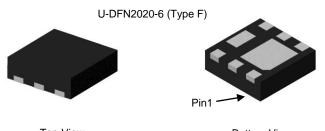
This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

## **Applications**

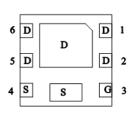
- DC/DC Converter
- Adaptor Switch
- Wireless Charging

#### **Mechanical Data**

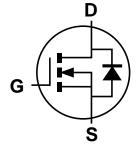
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.007 grams (Approximate)



Top View Bottom View



Pin Out Bottom View



Equivalent Circuit

### **Ordering Information** (Note 4)

Part Number	Package	Quantity per Reel
DMT6013LFDF-7	U-DFN2020-6 (Type F)	3000
DMT6013LFDF-13	U-DFN2020-6 (Type F)	10,000

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**

Site 1:



13 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	Н	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2:



13 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 8 = 2018)

W = Week (ex: a = week27; z represents week 52 and 53) X = Internal code (ex: U = Monday)

Date Code Key

Date Code Hoy									
Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	7	8	9	0	1	2	3	4	5

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	ID	10.0 8.0	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	1		I <sub>DM</sub>	60	Α
Maximum Body Diode Continuous Current			Is	10	Α
Pulsed Body Diode Forward Current (10µs Pulse, Du	uty Cycle = 1%)		I <sub>SM</sub>	60	А
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	11.7	Α		
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	6.8	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit	
Total Bower Dissination (Note 5)	$T_A = +25^{\circ}C$	р	0.9	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	$P_{D}$	0.58	VV	
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>OJA</sub>	139	°C/W	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	р	1.9	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	$P_{D}$	1.2	V V	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\Theta JA}$	67	°C/W	
Total Power Dissipation (Note 6)	$T_{C} = +25^{\circ}C$	$P_{D}$	10.8	W	
Thermal Resistance, Junction to Case (Note 6)		$R_{\Theta JC}$	11.6	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

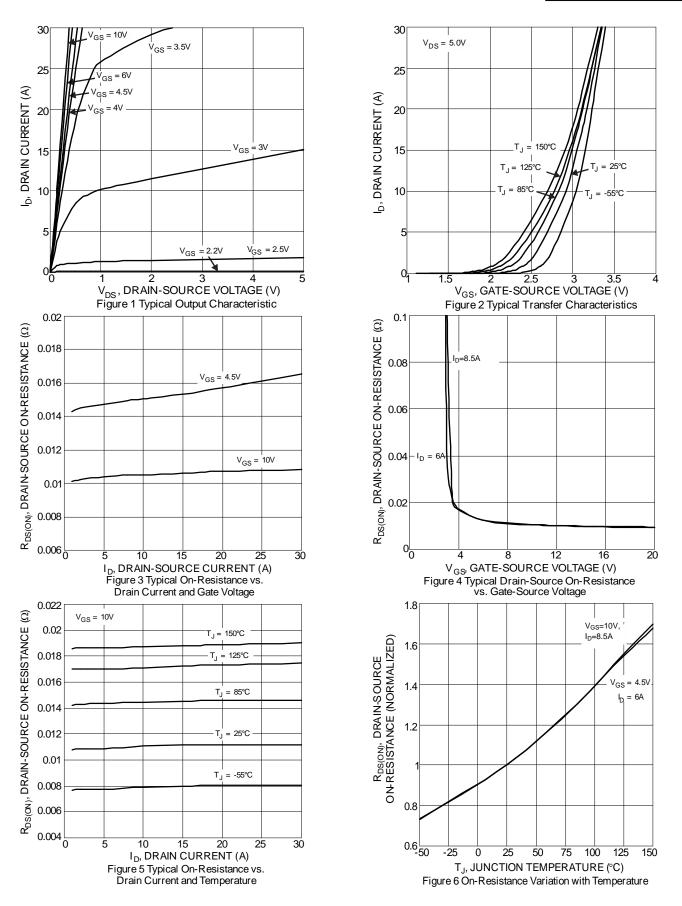
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	•		•	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	2.3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			12.2	15	mΩ	$V_{GS} = 10V, I_D = 8.5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		16.9	21.5	11122	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>		1081	_		V 20V V 0V	
Output Capacitance	Coss	1	253	_	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		22	_		1 - 1101112	
Gate Resistance	Rg		1.22	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$		15	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		8.5	_	nC	V 20V I 40A	
Gate-Source Charge	Qgs	_	2.2	_	IIC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	$Q_{gd}$	_	4.4	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.3	_			
Turn-On Rise Time	t <sub>R</sub>	_	6.5	_		$V_{GS} = 10V, V_{DD} = 30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	15.8	_	ns	$R_g = 6\Omega, I_D = 10A$	
Turn-Off Fall Time	t <sub>F</sub>	_	6.1	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	19.7	_	ns	1 100 1:/14 1000/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	9.5	_	nC	I <sub>S</sub> = 10A, di/dt = 100A/μs	

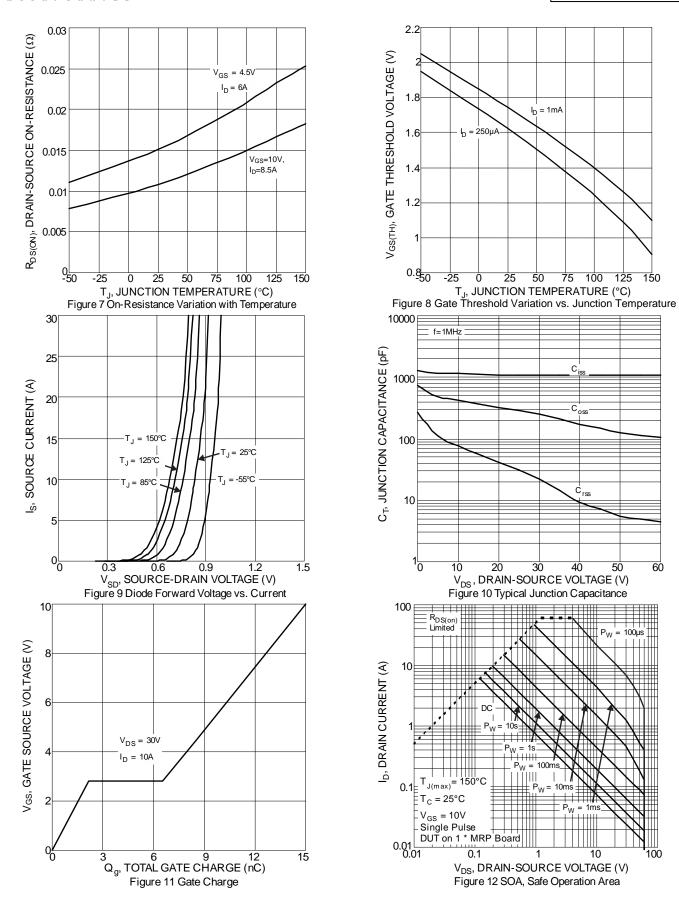
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.







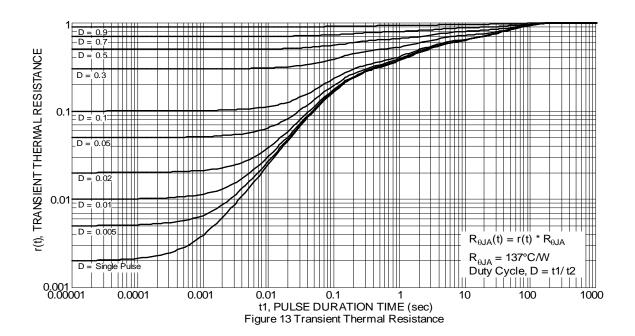


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June 2018

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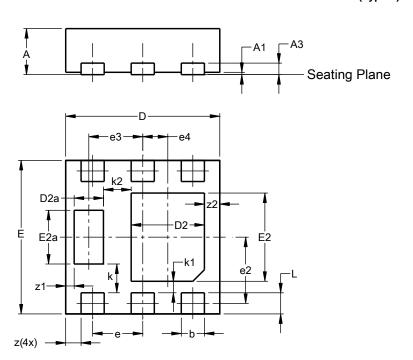




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type F)

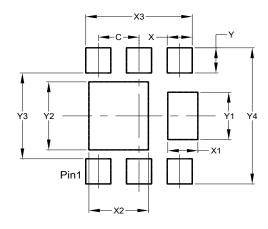


	U-DFN	2020-6						
	_	pe F)						
Dim	Min	Min Max Typ						
Α	0.57							
A1	0.00	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.65 0.75 0.70						
е		0.65 BS	С					
e2	C	).863 BS	SC					
е3		0.70 BS	С					
e4	C	).325 BS	SC					
k		0.37 BS	C					
k1		0.15 BS	С					
k2		0.36 BS	С					
L	0.225	0.325	0.275					
Z	0.20 BSC							
<b>z</b> 1	C	).110 BS	SC SC					
z2		0.20 BS	С					
All C	Dimens	ions in	mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type F)



Dimensions	Value
Dilliensions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

June 2018

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